PDFN3×3A-8L P MOS

P-Channel Enhancement Mode Field Effect Transistor in a PDFN3×3A-8L Plastic Package.

V_{DS} (V) = -16V I_D =-49.5A (V_{GS} = ± 12V)

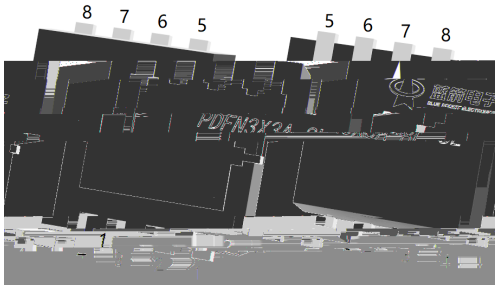
$R_{DS(ON)}$@-4.5V≤8mΩ(Typ. 6.6mΩ)

$R_{DS(ON)}$@-2.5V≤15mΩ(Typ. 9.8mΩ)

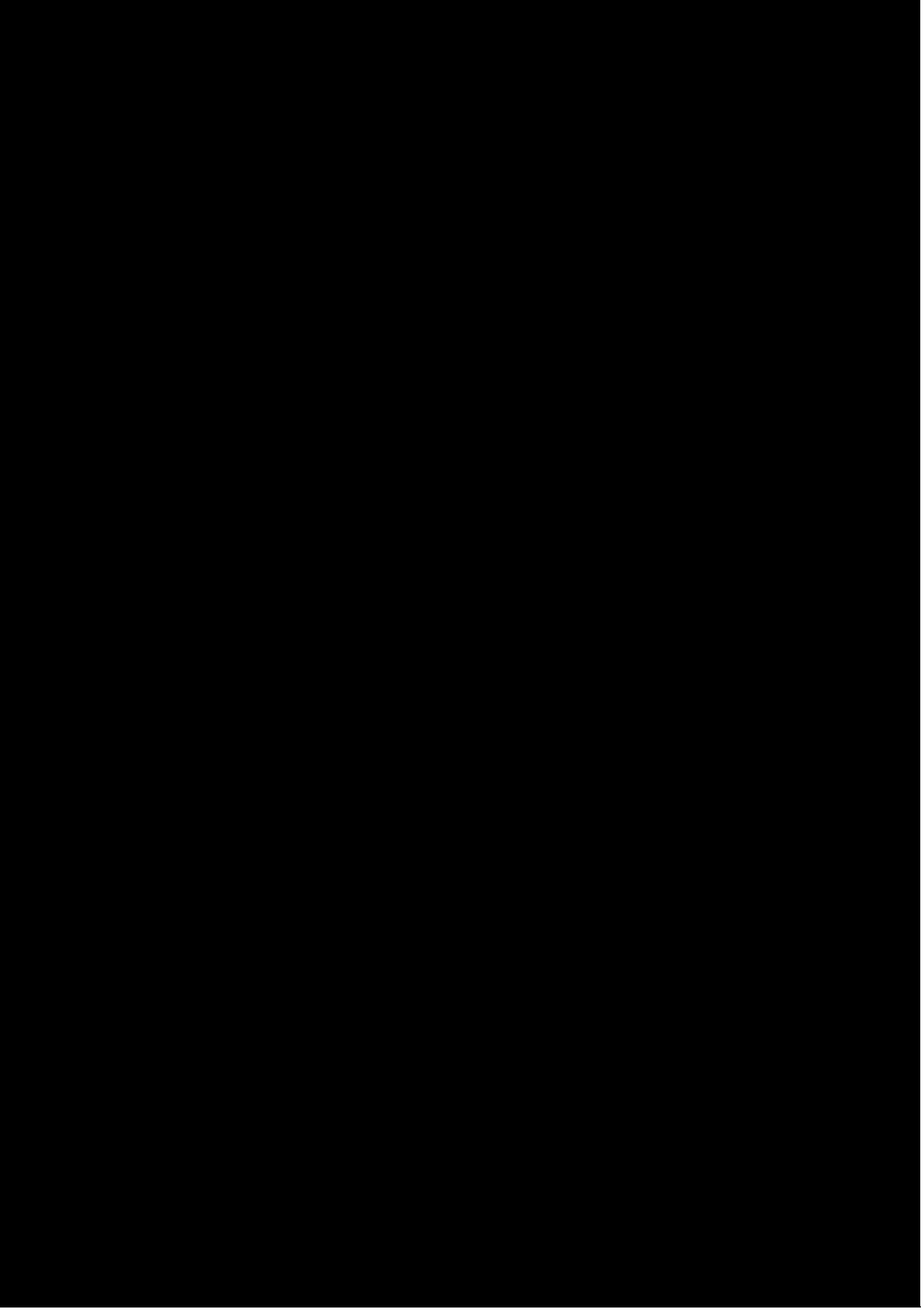
HF Product.

/

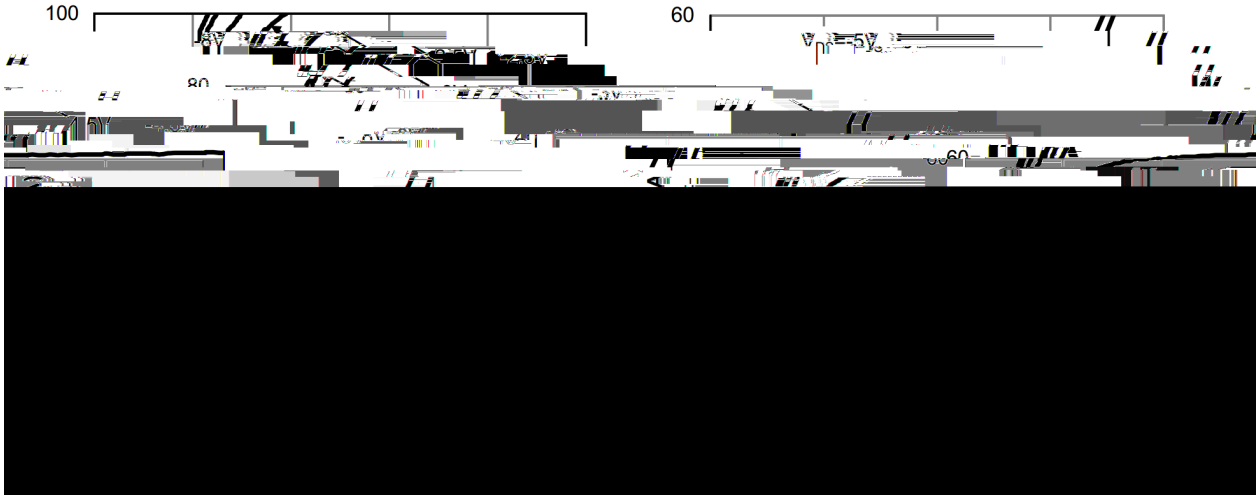
Notebook AC-in load switch,Battery protection charge/discharge.

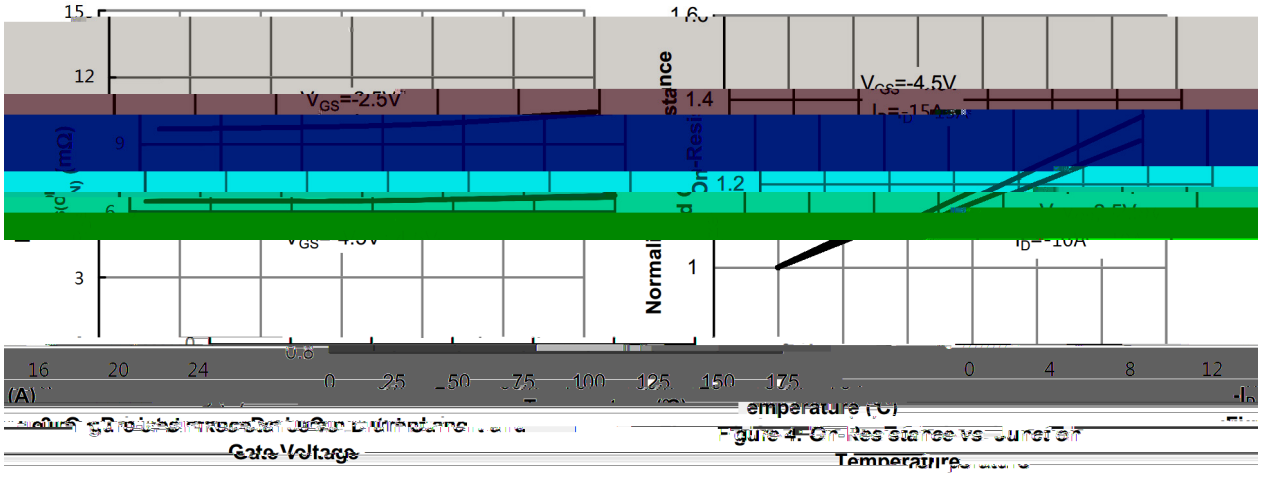


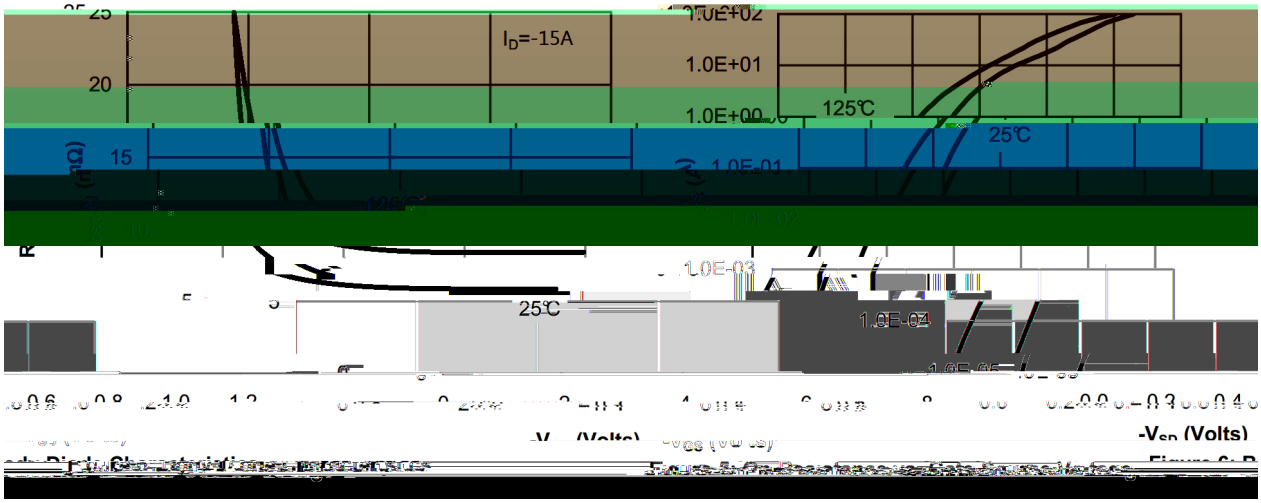
See Marking Instructions.

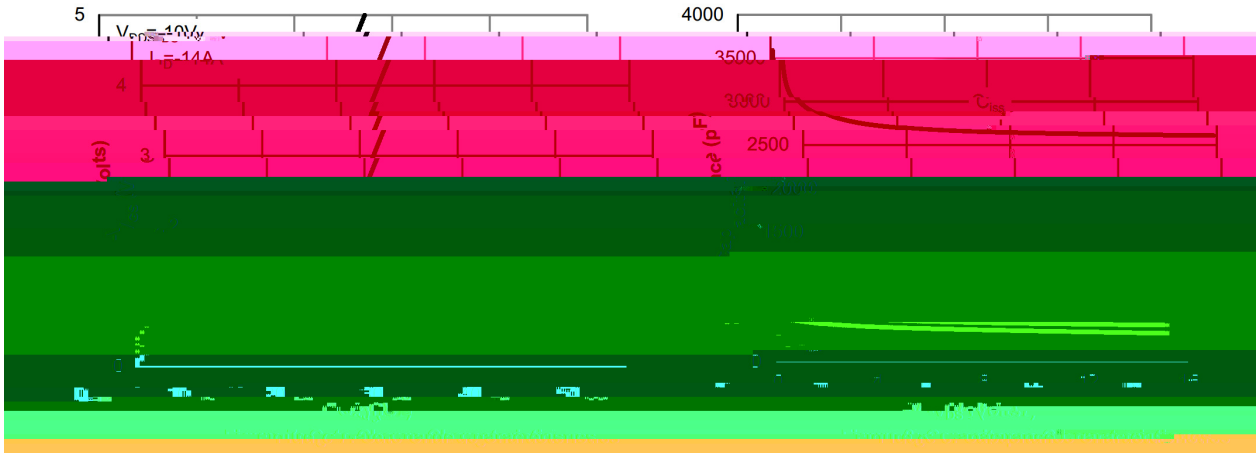


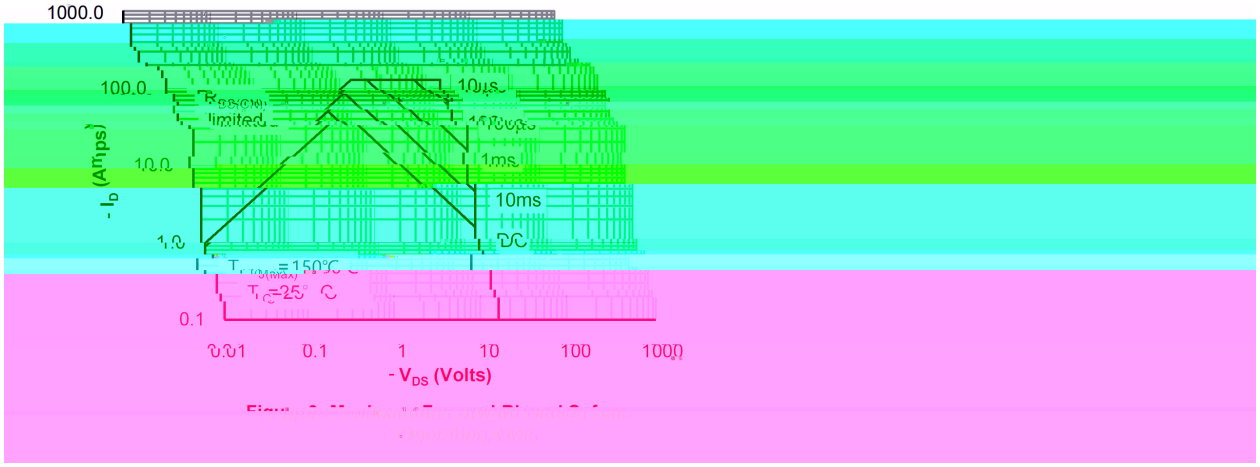
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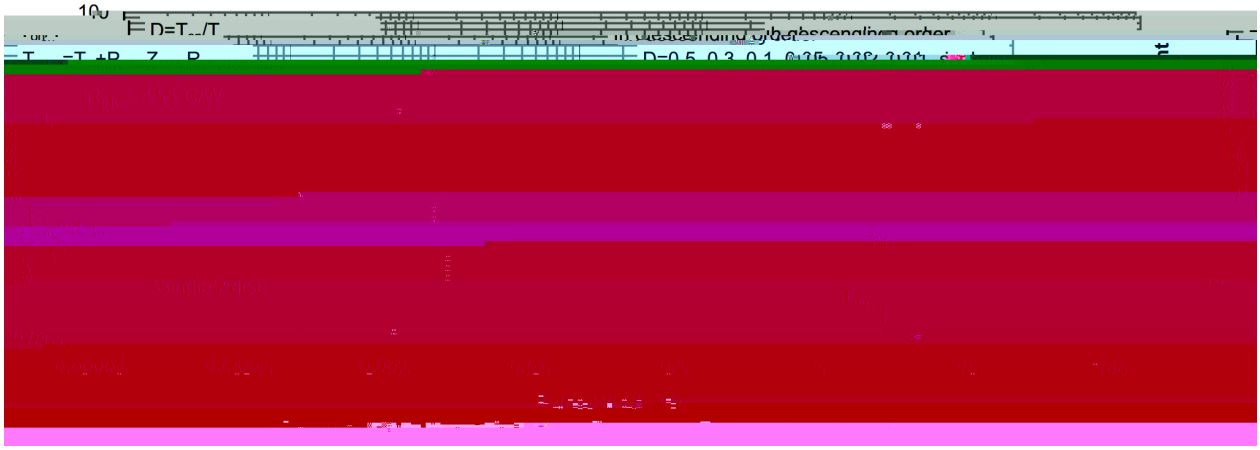



V_{GS}=-2.5V
V_{GS}=-4.5V
I_D=-15A
I_D=-10A
Normalized On-Resistance
Gate Voltage
Temperature


I_D=-15A
125℃
25℃
-V_{SD} (Volts)

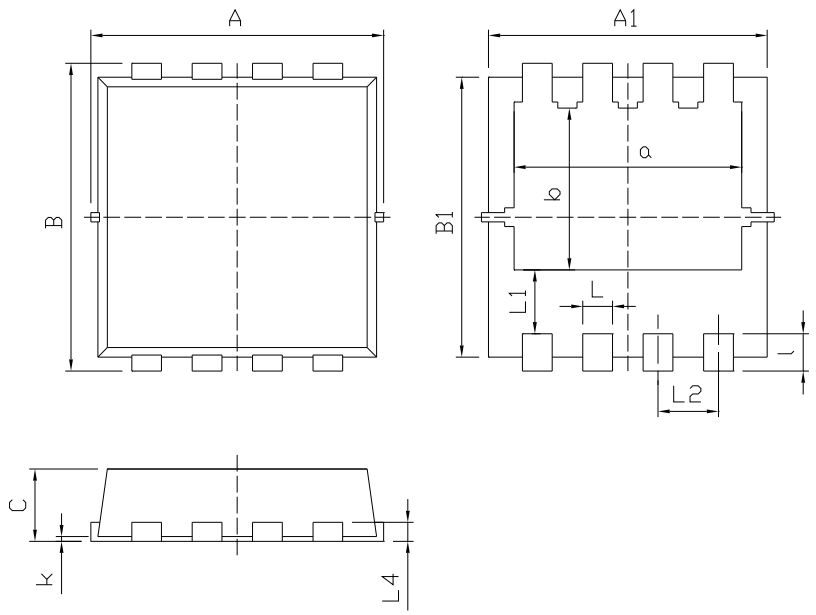

5
4
3
4000
3500
2500


1000.0
100.0
10µs
1ms
10ms
1.0
0.1
0.1
1
10
100
- V_DS (Volts)


D=T

PDFN3X3A-8L

Unit:mm



Dimensions In Millimeterer			
Symbol	MIN	TYP	MAX
A	3.20	3.30	3.40
A1	3.10	3.15	3.20
B	3.20	3.30	3.40
B1	2.95	3.00	3.05
C	0.75	0.80	0.85
L	0.25	0.30	0.35
L1	-	-	0.75
L2	0.55	0.65	0.75
L4	0.14	0.15	0.20
a	2.35	2.45	2.55
b	1.635	1.735	1.835
k	0.00	-	0.05
l	0.30	0.40	0.50

Rev.00 202011



BR

080P016

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Note:

BR:	Company Code
080P016:	Product Type Code
****:	Lot No. Code, code change with Lot No.

Rev.A Aug.-2025